



DPBT8105

1A PNP SURFACE MOUNT TRANSISTOR

Features

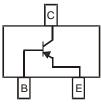
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- High Collector Current Rating
- Complementary Version Available (DNBT8105)
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green Device" (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



Top View



Device Schematic

Ordering Information (Note 3)

Part Number	Case	Packaging			
DPBT8105-7	SOT23	3000/Tape & Reel			

1. No purposefully added lead.

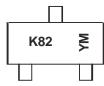
2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

Data Coda Kov

Notes:



K82 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: S = 2005) M = Month (ex: 9 = September)

Dale Coue Key		-										
Year	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	R	S	Т	U	V	W	Х	Y	Z	А	В	С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
	Uan	1.00	Intal	лμі	inay	oun	oui	Aug	Ocp	001	-	Dec
Code	1	2	3	1	5	6	7	Q	a	\cap	N	



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-5	V
Collector Current - Continuous	I _C	-1	A
Peak Pulse Collector Current	I _{CM}	-2	A

Thermal Characteristics

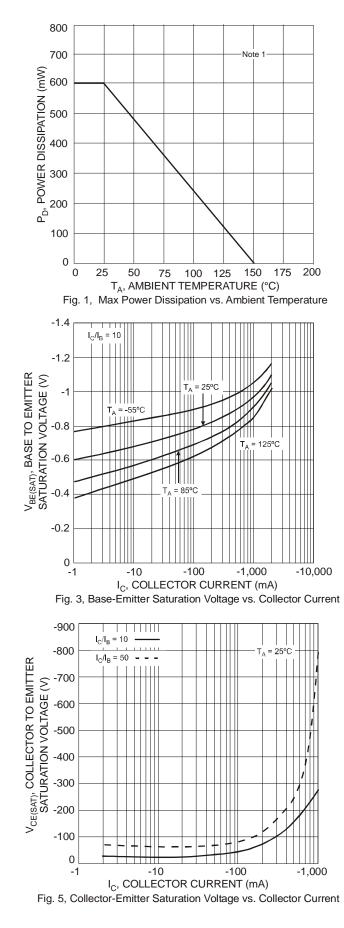
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4) @ $T_A = 25^{\circ}C$	PD	600	mW
Thermal Resistance, Junction to Ambient (Note 4) @ $T_A = 25^{\circ}C$	$R_{ ext{ heta}JA}$	209	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	O°

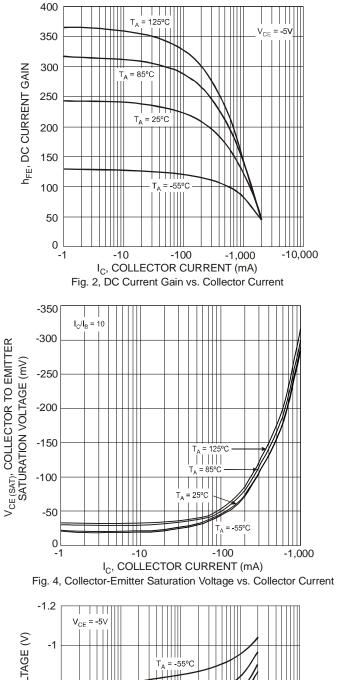
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					·
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-80	_	V	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-60	_	V	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-5	_	V	$I_{E} = -100 \mu A, I_{C} = 0$
Collector Cutoff Current	I _{CBO}	_	-100	nA	$V_{CB} = -60V, I_E = 0$
Collector Cutoff Current	I _{CES}	_	-100	nA	$V_{CE} = -60V$
Emitter Cutoff Current	I _{EBO}	_	-100	nA	$V_{EB} = -4V, I_{C} = 0$
ON CHARACTERISTICS (Note 5)					
DC Current Gain	hFE	100 100 80 30	 300 	_	$I_{C} = -1mA, V_{CE} = -5V$ $I_{C} = -500mA, V_{CE} = -5V$ $I_{C} = -1A, V_{CE} = -5V$ $I_{C} = -2A, V_{CE} = -5V$
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		-0.3 -0.6	V	$I_{C} = -500$ mA, $I_{B} = -50$ mA $I_{C} = -1$ A, $I_{B} = -100$ mA
Base-Emitter Saturation Voltage	V _{BE(SAT)}		-1.2	V	I _C = -1A, I _B = -100mA
Base-Emitter Turn On Voltage	V _{BE(ON)}		-1.0	V	I _C = -1A, V _{CE} = -5V
SMALL SIGNAL CHARACTERISTICS					·
Output Capacitance	Cobo	_	12	pF	V _{CB} = -10V, f = 1.0MHz
Current Gain-Bandwidth Product	f⊤	150	_	MHz	$V_{CE} = 10V, I_C = 50mA, f = 100MHz$

 Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
 Short duration pulse test used to minimize self-heating effect. Notes:







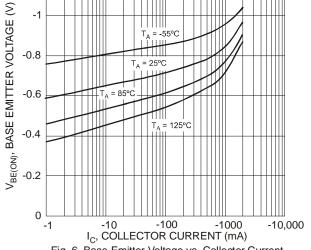
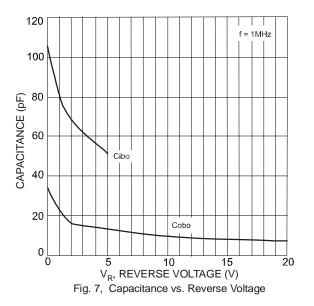
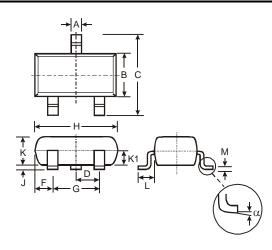


Fig. 6, Base-Emitter Voltage vs. Collector Current



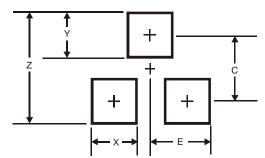


Package Outline Dimensions



SOT-23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
ĸ	0.903	1.10	1.00			
K1	-	-	0.400			
L	0.45	0.61	0.55			
М	0.085	0.18	0.11			
α	0°	8°	-			
All	All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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